# 2SD1773

## Silicon NPN triple diffusion planar type darlington

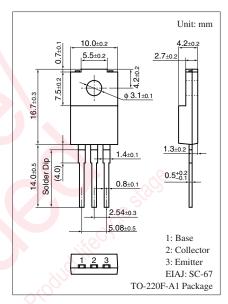
For midium speed switching Complementary to 2SB1193

#### ■ Features

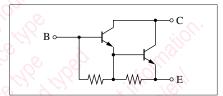
- High forward current transfer ratio hFE
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw

### ■ Absolute Maximum Ratings $T_C = 25$ °C

| Parameter                             | Symbol           | Rating      | Unit |  |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V <sub>CBO</sub> | 120         | V    |  |
| Collector-emitter voltage (Base open) | V <sub>CEO</sub> | 120         | V    |  |
| Emitter-base voltage (Collector open) | $V_{EBO}$        | 7           | V    |  |
| Collector current                     | $I_{C}$          | 8           | A    |  |
| Peak collector current                | $I_{CP}$         | 12          | A    |  |
| Collector power                       | $P_{C}$          | 50          | W    |  |
| dissipation $T_a = 25$ °C             |                  | 2.0         |      |  |
| Junction temperature                  | T <sub>j</sub>   | 150         | °C   |  |
| Storage temperature                   | $T_{stg}$        | -55 to +150 | °CO  |  |
|                                       |                  |             |      |  |



#### Internal Connection

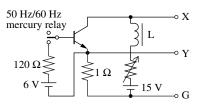


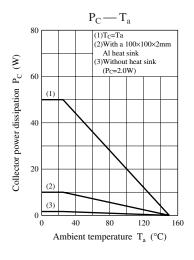
### ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

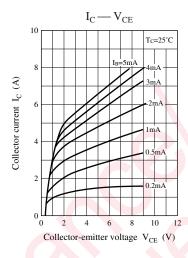
| Parameter                                    | Symbol                | Conditions  | Min   | Тур | Max    | Unit |
|--|-----------------------|---|-------|-----|--------|------|
| Collector-emitter sustaining voltage *       | V <sub>CEO(SUS)</sub> | $I_C = 2 \text{ A}, R_{BE} = \infty, L = 10 \text{ mH}$             | 120   | 1/2 | ,      | V    |
| Emitter-base voltage (Collector open)        | V <sub>EBO</sub>      | $I_{\rm E} = 50 \text{ mA}, I_{\rm C} = 0$                          | 7     | 0,  |        | V    |
| Collector-base cutoff current (Emitter open) | $I_{CBO}$             | $V_{CB} = 120 \text{ V}, I_E = 0$                                   |       | 0-  | 100    | μΑ   |
| Collector-emitter cutoff current (Base open) | $I_{CEO}$             | $V_{CE} = 100 \text{ V}, R_{BE} = \infty$                           | ~ 50  |     | 10     | μΑ   |
| Forward current transfer ratio               | $h_{FE}$              | $V_{CE} = 3 \text{ V}, I_{C} = 4 \text{ A}$                         | 1 000 |     | 20 000 | _    |
| Collector-emitter saturation voltage         | V <sub>CE(sat)1</sub> | $I_C = 4 \text{ A}, I_B = 8 \text{ mA}$                             |       |     | 1.5    | V    |
| - align                                      | V <sub>CE(sat)2</sub> | $I_C = 8 \text{ A}, I_B = 80 \text{ mA}$                            |       |     | 3.0    |      |
| Base-emitter saturation voltage              | V <sub>BE(sat)1</sub> | $I_C = 4 \text{ A}, I_B = 8 \text{ mA}$                             |       |     | 2.0    | V    |
| No.  | V <sub>BE(sat)2</sub> | $I_C = 8 \text{ A}, I_B = 80 \text{ mA}$                            |       |     | 3.5    |      |
| Transition frequency                         | $f_T$                 | $V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ A}, f = 1 \text{ MHz}$     |       | 20  |        | MHz  |
| Turn-on time                                 | t <sub>on</sub>       | $I_C = 4 \text{ A}, I_{B1} = 8 \text{ mA}, I_{B2} = -8 \text{ mA},$ |       | 0.7 |        | μs   |
| Storage time                                 | t <sub>stg</sub>      | $V_{CC} = 50 \text{ V}$   |       | 6.0 |        | μs   |
| Fall time                                    | t <sub>f</sub>        |   |       | 2.0 |        | μs   |

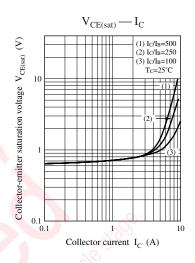
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

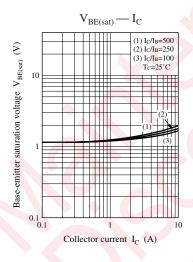
2. \*: V<sub>CEO(SUS)</sub> Test circuit

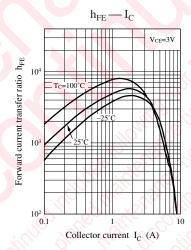


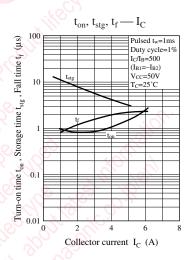


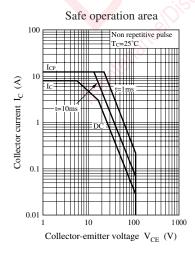


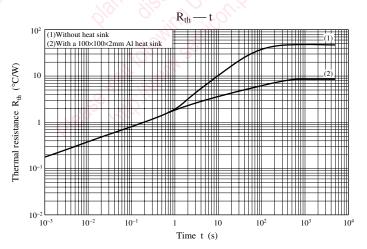












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